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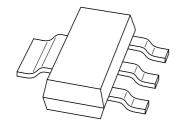
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PZTA14NPN Darlington transistor

Product data sheet Supersedes data of 1997 Sep 04 1999 Apr 14



NPN Darlington transistor

PZTA14

FEATURES

• High current (max. 500 mA)

• Low voltage (max. 30 V).

APPLICATIONS

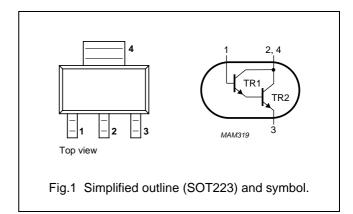
• Pre-amplifiers requiring high input impedance.

DESCRIPTION

NPN Darlington transistor in a SOT223 plastic package. PNP complement: PZTA64.

PINNING

PIN	DESCRIPTION				
1	base/input				
2, 4	collector/output				
3	emitter/ground				



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	30	V
V _{CES}	collector-emitter voltage	V _{BE} = 0	_	30	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
I _C	collector current (DC)		_	500	mA
I _{CM}	peak collector current		_	800	mA
I _B	base current (DC)		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	1.25	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

NPN Darlington transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	100	K/W
R _{th j-s}	thermal resistance from junction to soldering point		19	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

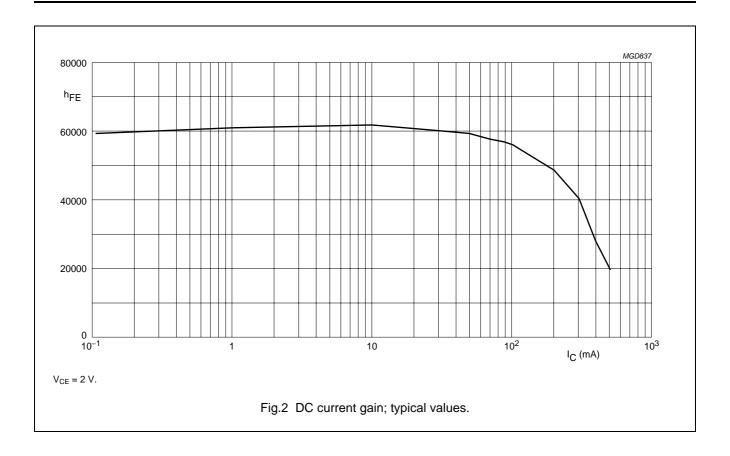
CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	_	100	nA
I _{CES}	collector cut-off current	V _{BE} = 0; V _{CE} = 30 V	_	100	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 10 V	_	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; (see Fig.2)			
		I _C = 10 mA	10000	_	
		I _C = 100 mA	20000	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 0.1 \text{ mA}$	_	1.5	V
V _{BEon}	base-emitter on-state voltage	I _C = 100 mA; V _{CE} = 5 V	_	2	V
f _T	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	125	_	MHz

NPN Darlington transistor

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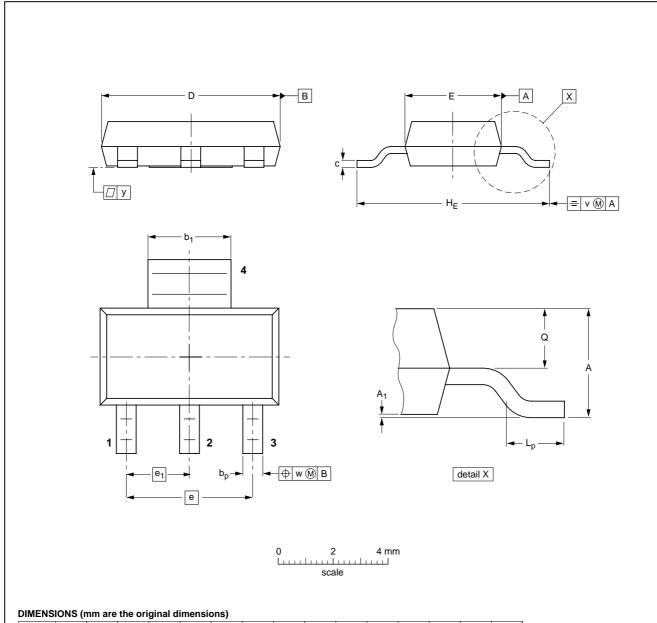
NPN Darlington transistor

PZTA14

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



UNIT	Α	A ₁	bp	b ₁	С	D	E	е	e ₁	HE	Lp	Q	v	w	у
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22		3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT223			SC-73			97-02-28 99-09-13

NPN Darlington transistor

PZTA14

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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